S4	1110	S1 and (("sio" or (silicon adj (dioxide or oixde))) near ("sin" or (silicon adj nitride)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/18 15:43
S5	845	S4 and (("si" or silicon) near substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/18 15:44
S6	832	S5 and (etch or etching or remove or removing or planar or planarization)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/18 15:46
S7	833	S5 and (etch or etching or remove or removing or planar or planarization or "cmp" or polish or polishing)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/18 15:47
S8	398	S7 and (etch or etching or remove or removing or planar or planarization or "cmp" or polish or polishing) with ((("sio" or (silicon adj (dioxide or oixde))) and ("sin" or (silicon adj nitride))))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/19 10:24